	Type	L #	Hits	Search Text	DBs
1	BRS	L1	5	ko near kwan.in.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
2	BRS	L2	163	(substrate or wafer) near25 (metal near cluster$1)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
3	BRS	L3	16	(substrate or wafer) near25 (remov$3) near15 (metal near cluster$1)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
4	BRS	L4	20968	(substrate or wafer) near25 (remov$3) near15 (metal)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB

	Type	L #	Hits	Search Text	DBs
5	BRS	L5	23	((substrate or wafer) near25 (remov$3) near15 (metal)) near35 (quantum)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
6	BRS	L6	189	((substrate or wafer) near25 (remov$3) near15 (metal)) near15 (oxide) near15 (poly$5)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
7	BRS	L7	8	(heat$3) near5 ((substrate or wafer) near25 (remov$3) near15 (metal)) near15 (oxide) near15 (poly$5)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
8	BRS	L8	221	(heat$3) near5 ((substrate or wafer) near25 (remov$3) near15 (metal)) near15 (oxide)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB

	Type	L #	Hits	Search Text	DBs
9	BRS	L9	29	(heat$3) near5 (silicon) near15 ((substrate or wafer) near25 (remov$3) near15 (metal)) near15 (oxide)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
10	BRS	L10	69543	(substrate or wafer) near15 (density)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
11	BRS	L11	4332	(heat$3) near15 (substrate or wafer) near15 (density)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
12	BRS	L12	11	(heat$3) near15 (substrate or wafer) near15 (density) near25 (remov$3) near15 (silicon)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB

	Type	L #	Hits	Search Text	DBs
13	BRS	L13	129	(heat$3) near15 (substrate or wafer) near15 (density) near25 (remov$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
14	BRS	L14	1	13 and (quantum near dot)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
15	BRS	L15	2	11 and (quantum near dot)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
16	BRS	L16	1115009	(absorb$3) (metal or gold) near20 (density)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB

	Type	L #	Hits	Search Text	DBs
17	BRS	L17	532	(absorb$3) near15 (metal or gold) near20 (density)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
18	BRS	L18	48	((absorb$3) near15 (metal or gold) near20 (density)) near25 (heat$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
19	BRS	L19	4219	((substrate) near20 (density)) near25 (heat$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
20	BRS	L20	137	((silicon near substrate) near20 (density)) near25 (heat$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB

	U	1	Document ID	Title
1			US 20050003620 A1	Methods of forming quantum dots in semiconductor devices
2			US 20020005213 A1	SINTERED SILICON CARBIDE AND METHOD FOR CLEANING THE SAME IN WET CONDITION
3			US 6528387 B1	SOI substrate and process for preparing the same, and semiconductor device and process for preparing the same
4			US 6419757 B2	Method for cleaning sintered silicon carbide in wet condition
5			US 6117796 A	Removal of silicon oxide
6			US 5736454 A	Method for making a silicon dioxide layer on a silicon substrate by pure water anodization followed by rapid thermal densification
7			JP 02111034 A	MANUFACTURE OF SEMICONDUCTOR DEVICE

	U	1	Document ID	Title
8	X		JP 10074835 A	Multilayer interconnection structure formation method using high density plasma CVD for VLSI manufacture – involves heating substrate in inert gas atmosphere to remove excessive hydrogen from silicon film
9	X		JP 08078359 A	Semiconductor device mfg method e.g. SRAM – involves forming cobalt silicide by reaction between cobalt@ film and electrically conductive silicon domain, heat treating substrate and removing excess cobalt, giving high integration density IC
10	X		JP 52126183 A	Semiconductor device mfr. applicable to an integrated circuit – includes formation of heat resistance synthetic resin layer for depositing metal layers
11	X		JP 73042021 B	Arsenic diffusion into semiconductors – using relatively low temp process